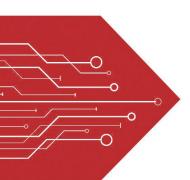
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Brodnet data speet

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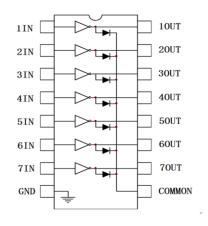
GENERAL DESCRIPTION

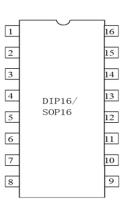
ULN2003 是单片集成高耐压、大电流达林顿管阵列,电路内部包含 7 个独立的达林顿管驱动单路。电路内部设计有钳位二极管,可用于驱动继电器、步进电机等电感性负载,将达林顿管并联可实现更高的输出电流能力。该电路可广泛应用于继电器驱动、照明驱动、显示屏驱动(LED)、步进电机驱动和逻辑缓冲器。ULN2003 的每一路达林顿管串联一个 2.7K 的基极电阻,在 5V 的工作电压下可直接与 TTL/CMOS电路连接,可直接处理标准逻辑缓冲器所处理的数据。

FEATURES

- 宽输入耐压: 0~30V, Ta=25℃
- 输出最大电流: 500MA, Ta=25℃

- 输出关闭状态耐压: 50V Ta=25℃
- 输入兼容 TTL/CMOS 逻辑信号





PIN CONFIGURATION

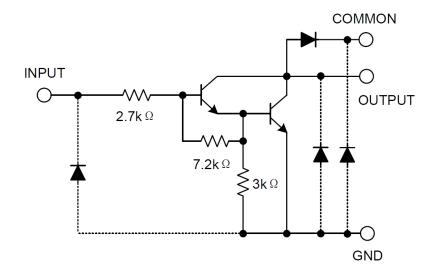
SOP16 DIP16	管脚 定义	管脚功 能描述	SOP16 DIP16	管脚 定义	管脚功 能描述
1	1 I N	1 通道输入	16	10UT	1 通道输出
2	2IN	2 通道输入	15	20UT	2 通道输出
3	3IN	3 通道输入	14	30UT	3 通道输出
4	4IN	4 通道输入	13	40UT	4 通道输出
5	5IN	5 通道输入	12	50UT	5 通道输出
6	6IN	6 通道输入	11	60UT	6 通道输出
7	7IN	7 通道输入	10	70UT	7 通道输出
8	GND	接电源地	9	COMMON	钳位二极管公共端

极限参数

极限参数	符号	极限值	单位
输入电压	V_{IN}	30	V
输出电压	V _{CE}	50	V
集电极电流	I _C	500	mA
基极电流	$I_{\mathbf{B}}$	25	mA
工作温度	T_{A}	-40~85	$^{\circ}$
存储温度	T _S	-65∼150	${\mathbb C}$
焊接温度	T_{W}	260, 10s	$^{\circ}$

注:极限参数是指无论在任何条件下都不能超过的极限值。如果超过此极限值,将有可能造成产品劣化等物理性损伤; 同时在接近极限参数下,不能保证芯片可以正常工作。

原理逻辑图



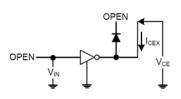
电学特	性

(**直流电学特性:** T_A=25℃)

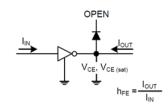
符号	项目	测试条件		测试电路	最小值	典型值	最大值	单位
	输出高	\/ -E0\/	Ta=25 ℃	1	-	0	50	μΑ
I _{CEX}	漏电电流	V _{CE} =50V	Ta=85 ℃	1	-	0	100	μΑ
	松山低	I _{OUT} =350mA, I _{IN} =500μA		2	-	1.0	1.6	V
V _{CE(SAT)}	输出低 电平电压	I _{OUT} =200mA, I _{IN} =350μA			-	0.9	1.3	V
	电干电压 	I _{OUT} =100mA, I _{IN} =250μA			-	0.8	1.1	V
I _{IN(ON)}	输入电流	V _{IN} =3.85\	V, I _{OUT} =350mA	3	-	0.7	1.35	mA
I _{IN(OFF)}	- 柳八电孤	I _{OUT} =50	0μA, Ta=85℃	4	50	63	-	μΑ
			I _{OUT} =200mA		-	1.8	2.4	٧
V _{IN(ON)}	输入电压	V _{CE} =2V	I _{OUT} =250mA	5	-	1.85	2.7	٧
			I _{OUT} =300mA		-	1.9	3.0	V
IR	钳位二极管	\/D_F0\/	Ta=25 ℃	6	-	0	50	μΑ
IK	反向漏电流	VR=50V	Ta=85 ℃		-	0	100	μΑ
VF	钳位二极管压降	I _F =350mA	Ta=25 ℃	7	-	1.7	2.0	V
t _{on}	开启延迟时间	V _{OUT} =50V,R _L =125Ω,C _L =15pF		8	-	0.1	1	μs
t _{OFF}	关断延迟时间	V_{OUT} =50V, R_L =125 Ω , C_L =15pF		0	-	0.2	1	μs

测试方法

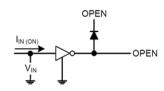
1. I_{CEX}



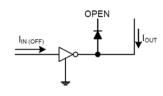
2. V_{CE (sat)}, h_{FE}



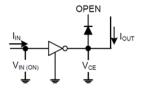
 $3.\ I_{IN\ (ON)}$



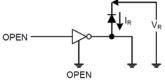
4. I_{IN (OFF)}



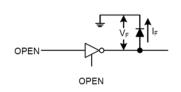
 $5.\ V_{IN\ (ON)}$



6. I_R



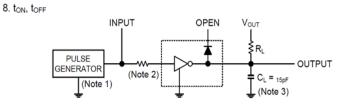
7. V_F

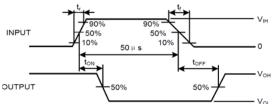


8. t_{ON} , t_{OFF} 注:

(1) 脉冲宽度为 50US, 占空比为 10%, 输出 负载 125Ω, tr<=20ns, tf<=20ns;

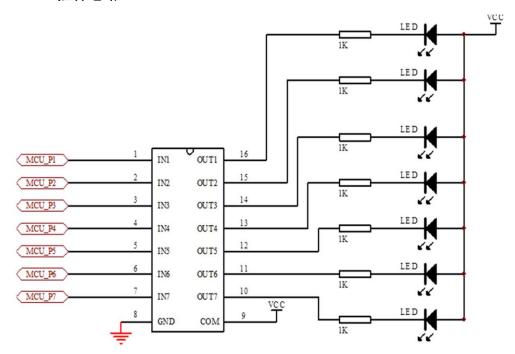
- (2) R=0, VIH=3V;
- (3) CL 包括探针和测试夹具的电容。





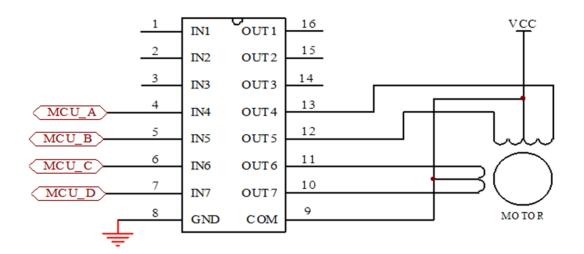
典型应用线路

1、 LED 驱动电路

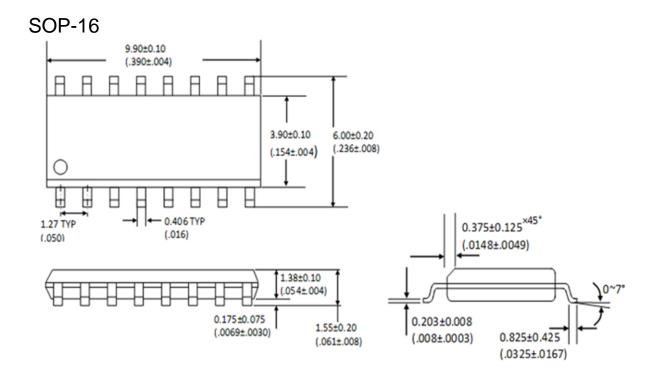


注: 1K 的电阻可根据 VCC 的电压和所需 LED 的电流进行调整。

2、 步进电机驱动电路



PACKAGE MECHANICAL DATA

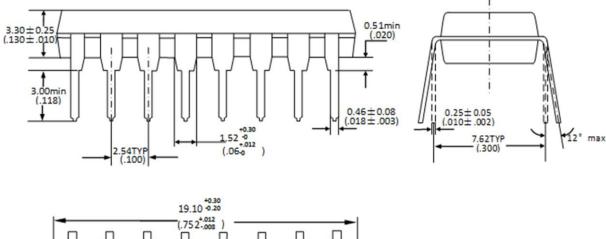


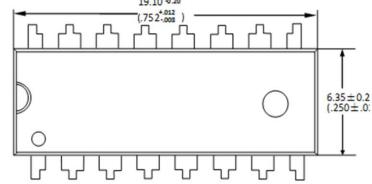
REEL SPECIFICATION

P/N	PKG	QTY
ULN2003	SOP-16	4000

PACKAGE MECHANICAL DATA

DIP-16





REEL SPECIFICATION

P/N	PKG	QTY
ULN2003	DIP-16	1000



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